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|---|-----|--|---|------------------|
| - | 21 | (semiconductor near laser) and (active near (layer or region or medium or film)) and (protection near (film or layer or region or medium)) and ridge and (refractive near (index or indice)) and (open\$5) and (shap\$4) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/04/04 10:46 |
| - | 3 | ("5029175" "5474954" "5805627").PN. | USPAT | 2003/04/04 10:40 |
| - | 23 | (semiconductor near laser) and (active near (layer or region or medium or film)) and (protection near (film or layer or region or medium)) and ridge and (refractive near (index or indice)) and (open\$5) and (shap\$4) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/04/04 10:49 |
| - | 57 | (semiconductor near laser) and substrate and (active near (layer or region or film or medium)) and (protection near (layer or region or film or medium)) and (ridge or stripe) and (refractive near (index or indice)) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/04/04 11:06 |
| - | 18 | (semiconductor near laser) and substrate and (active near (layer or region or film or medium)) and (protection near (layer or region or film or medium)) and ((ridge or stripe) WITH (refractive near (index or indice))) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/04/04 12:09 |
| - | 14 | (semiconductor near laser) and substrate and (protection near (layer or region or film or medium)) and ((ridge or stripe) WITH (refractive near (index or indice)) WITH (active near (layer or region or film or medium))) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/04/04 12:40 |
| - | 405 | (semiconductor near laser) and (active near (layer or region or medium or film)) and ((protect\$4 or dielectric) near (film or layer or region or medium)) and ridge and (refractive near (index or indice)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/11/13 09:31 |
| - | 61 | (semiconductor near laser) and (active near (layer or region or medium or film)) and (protection near2 (film or layer or region or medium)) and ridge and (refractive near (index or indice)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/11/13 10:34 |
| - | 5 | (semiconductor near laser) and (active near (layer or region or medium or film)) and (protection near2 dielectric near2 (film or layer or region or medium)) and ridge and (refractive near (index or indice)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/11/14 06:09 |

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|----------|------|--|---|------------------|
| - | 34 | (semiconductor near laser) and (active near (layer or region or medium or film)) and (protection near (film or layer or region or medium)) and ridge and (refractive near (index or indice)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/11/13 09:51 |
| - | 28 | ((semiconductor near laser) and (active near (layer or region or medium or film)) and (protection near (film or layer or region or medium)) and ridge and (refractive near (index or indice))) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/20 13:54 |
| - | 12 | (semiconductor near laser) and ((active near (layer or region or medium or film)) SAME (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and ridge and (refractive near (index or indice)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/20 10:37 |
| - | 21 | (semiconductor near laser) and ((active near (layer or region or medium or film)) AND (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and ridge and (refractive near (index or indice)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/20 15:02 |
| - | 17 | ((semiconductor near laser) and ((active near (layer or region or medium or film)) AND (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and ridge and (refractive near (index or indice))) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/20 14:24 |
| - | 10 | ((semiconductor near laser) and ((active near (layer or region or medium or film)) SAME (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and ridge and (refractive near (index or indice))) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/20 14:24 |
| - | 12 | (semiconductor near laser) and ((active near (layer or region or medium or film)) AND (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and (width same ridge) and (refractive near (index or indice)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/20 16:36 |
| - | 11 | ((semiconductor near laser) and ((active near (layer or region or medium or film)) AND (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and (width same ridge) and (refractive near (index or indice))) and 372/\$ | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/21 08:26 |
| - | 456 | (semiconductor near laser) and (active near (layer or region or medium or film)) and ((dielectric or insulat\$5 or protect\$5) near (film or layer or region or medium)) and ridge and (refractive near (index or indice)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/21 10:56 |
| - | 382 | (semiconductor near laser) and (active near (layer or region or medium or film)) and ((dielectric or insulat\$5 or protect\$5) near (film or layer or region or medium)) and ridge and (refractive near (index or indice)) AND substrate and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/21 10:59 |
| - | 0 | (semiconductor near laser) and (active near (layer or region or medium or film)) and (((dielectric or insulat\$5 or protect\$5) near (film or layer or region or medium)) same substrat) and ridge and (refractive near (index or indice)) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/22 13:14 |
| - | 284 | (semiconductor near laser) and (active near (layer or region or medium or film)) and (((dielectric or insulat\$5 or protect\$5) near (film or layer or region or medium)) same substrate) and ridge and (refractive near (index or indice)) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/22 13:18 |

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|---|-----|--|---|------------------|
| - | 131 | (semiconductor near laser) and (active near (layer or region or medium or film)) and (((dielectric or insulat\$5 or protect\$5) near (film or layer or region or medium)) same substrate same ridge) and (refractive near (index or indice)) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/22 13:21 |
| - | 29 | (semiconductor near laser) and (active near (layer or region or medium or film)) and (((dielectric or insulat\$5 or protect\$5) near (film or layer or region or medium)) same substrate same ridge same (refractive near (index or indice))) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/22 14:31 |
| - | 23 | ((semiconductor near laser) and (active near (layer or region or medium or film)) and (((dielectric or insulat\$5 or protect\$5) near (film or layer or region or medium)) same substrate same ridge same (refractive near (index or indice))) and width) and 372/\$ | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/22 14:31 |
| - | 6 | ((semiconductor near laser) and (active near (layer or region or medium or film)) and (((dielectric or insulat\$5 or protect\$5) near (film or layer or region or medium)) same substrate same ridge same (refractive near (index or indice))) and width) and 257/\$ | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/22 14:32 |
| - | 12 | (semiconductor near device) and (active near (layer or region or medium or film)) and (((dielectric or insulat\$5 or protect\$5) near (film or layer or region or medium)) same substrate same ridge same (refractive near (index or indice))) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/22 14:36 |
| - | 30 | (semiconductor near (device or laser)) and (active near (layer or region or medium or film)) and (((dielectric or insulat\$5 or protect\$5) near (film or layer or region or medium)) same substrate same ridge same (refractive near (index or indice))) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/22 14:41 |
| - | 344 | (semiconductor with optical) and substrate and (active near (layer or film or region or medium)) and ((protect\$5 or insulat\$5) near (film or layer or region or medium)) and ridge and refractive | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 10:54 |
| - | 114 | (semiconductor with optical) and substrate and (active near (layer or film or region or medium)) and ((protect\$5 or insulat\$5) near (film or layer or region or medium)) and (ridge or groove) and refractive and (stripe near shaped) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 13:23 |
| - | 0 | ((semiconductor with optical) and substrate and (active near (layer or film or region or medium)) and ((protect\$5 or insulat\$5) near (film or layer or region or medium)) and (ridge or groove) and refractive and (stripe near shaped)) and (open\$5 near center) and (open\$5 near rear) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 13:33 |
| - | 108 | ((semiconductor with optical) and substrate and (active near (layer or film or region or medium)) and ((protect\$5 or insulat\$5) near (film or layer or region or medium)) and (ridge or groove) and refractive and (stripe near shaped)) and width | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 13:38 |
| - | 90 | ((semiconductor with optical) and substrate and (active near (layer or film or region or medium)) and ((protect\$5 or insulat\$5) near (film or layer or region or medium)) and (ridge or groove) and refractive and (stripe near shaped)) and width) and 372/\$ | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 13:38 |
| - | 27 | (semiconductor near laser) and (active near (layer or region or medium or film)) and (protection near (film or layer or region or medium)) and ridge and (refractive near (index or indice)) and (open\$5) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/06/18 11:28 |